

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

EMH2408 —

N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- The EMH2408 incorporates a N-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting
- 1.8V drive
- Halogen free compliance

Specifications

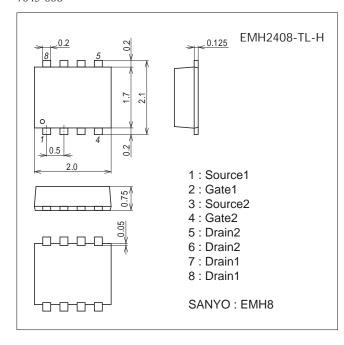
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		4	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	16	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.0	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity $< 200V^*$ ", so please take care when handling. * Machine Model

Package Dimensions

unit : mm (typ) 7045-006



Product & Package Information

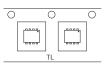
- : EMH8
- JEITA, JEDEC

• Package

• Minimum Packing Quantity : 3,000 pcs./reel

: -

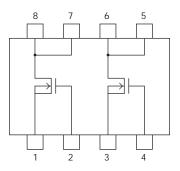
Packing Type : TL





Marking

Electrical Connection

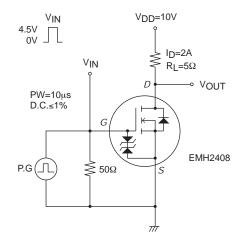


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Decemeter	Cumbral			11-14		
Parameter	Symbol	Conditions	min	typ max		Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V, ID=2A	2.0	3.4		S
	R _{DS} (on)1	ID=4A, VGS=4.5V		34	45	mΩ
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	ID=1A, VGS=2.5V		49	67	mΩ
	R _{DS} (on)3	ID=0.5A, VGS=1.8V		74	115	mΩ
Input Capacitance	Ciss			345		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		67		pF
Reverse Transfer Capacitance	Crss			52		pF
Turn-ON Delay Time	t _d (on)			9.2		ns
Rise Time	tr			60		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		30		ns
Fall Time	tf			38		ns
Total Gate Charge	Qg			4.7		nC
Gate-to-Source Charge	Qgs V _{DS} =10V, V _{GS} =4.5V, I _D =4A			0.65		nC
Gate-to-Drain "Miller" Charge	Qgd	1		1.6		nC
Diode Forward Voltage	VSD	IS=4A, VGS=0V		0.8	1.2	V

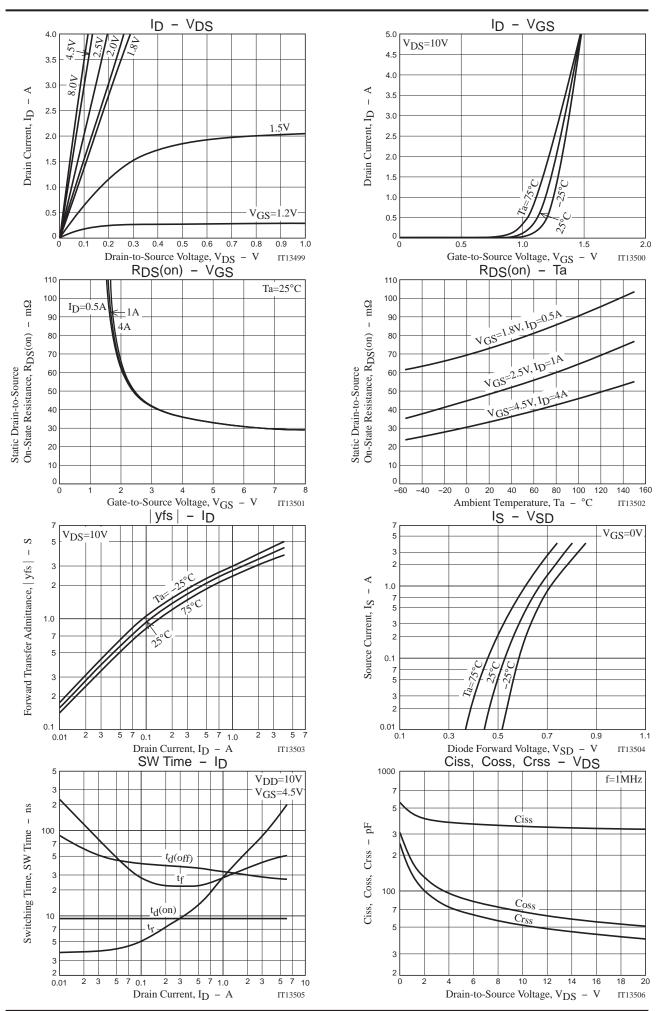
Electrical Characteristics at Ta=25°C

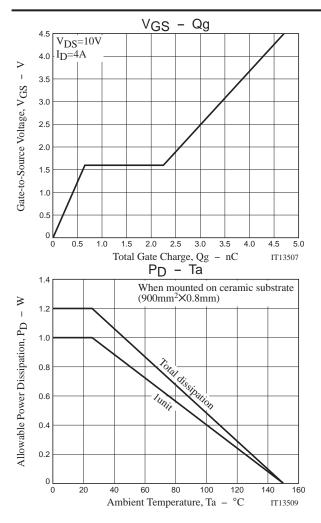
Switching Time Test Circuit

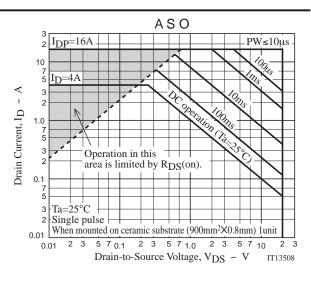


Ordering Information

Device	Package	Shipping	memo		
EMH2408-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free		







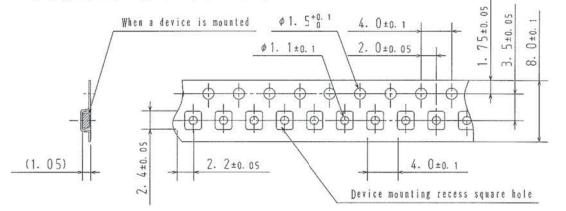
Embossed Taping Specification EMH2408-TL-H

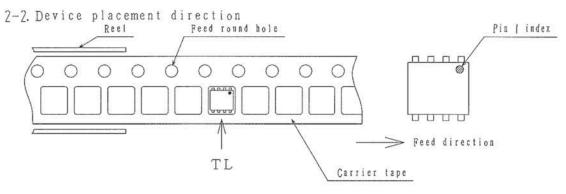
1. Packing Format

Package Name	Carrier Tape		imum Number of es contained (pcs)		Packing format			
	Type	Reel	[nner box	Quter box	Inn	er BOX	(C-1)	Outer BOX (A-7)
EMH8	MCP4	3, 000	15,000	90,000	5 reel	s contain	ed	6 inner boxes contained
					Dinen	sions:mm	(externa	1) Dimensions:mm (external)
					18	3×72>	< 185	440×195×210
			Reel	label, [(nner b	ox label		er box label
Packing me	thod			(u 1	nit:m	n)	The	s a label at the time of factory shipmen form of a label may change in physical ribution process.
•			-	6	59			108
	Orig	No. tity			Initiation III III IIIIIIIIIIIIIIIIIIIIIIIIIIIII	*****) escriptio	n shows	TYPE CODE
			[] []	Label		PARTICIPATION - A	Phase	
				LEAD FRE		JEITA I	in minimum and a second	A
				LEAD FRE	EE 4	JEITA I	hase 3	

2. Taping configuration

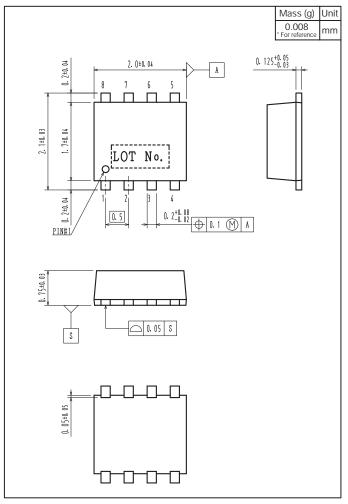
2-1. Carrier tape size (unit:mm)



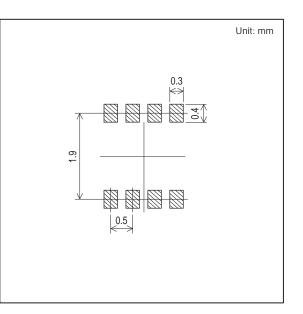


Those with pin 1 index on the feed hole side TL

Outline Drawing EMH2408-TL-H



Land Pattern Example



Note on usage : Since the EMH2408 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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